

Welcome to [E-XFL.COM](#)

Understanding [Embedded - Microprocessors](#)

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	Signal Processing; SPE
RAM Controllers	DDR, DDR2, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8548vuaqg

- Dedicated single data rate SDRAM controller
- Parity support
- Default boot ROM chip select with configurable bus width (8, 16, or 32 bits)
- Four enhanced three-speed Ethernet controllers (eTSECs)
 - Three-speed support (10/100/1000 Mbps)
 - Four controllers designed to comply with IEEE Std. 802.3®, 802.3u, 802.3x, 802.3z, 802.3ac, and 802.3ab
 - Support for various Ethernet physical interfaces:
 - 1000 Mbps full-duplex IEEE 802.3 GMII, IEEE 802.3z TBI, RTBI, and RGMII
 - 10/100 Mbps full and half-duplex IEEE 802.3 MII, IEEE 802.3 RGMII, and RMII
 - Flexible configuration for multiple PHY interface configurations. See [Section 8.1, “Enhanced Three-Speed Ethernet Controller \(eTSEC\) \(10/100/1Gb Mbps\)—GMII/MII/TBI/RGMII/RTBI/RMII Electrical Characteristics,”](#) for more information.
 - TCP/IP acceleration and QoS features available
 - IP v4 and IP v6 header recognition on receive
 - IP v4 header checksum verification and generation
 - TCP and UDP checksum verification and generation
 - Per-packet configurable acceleration
 - Recognition of VLAN, stacked (queue in queue) VLAN, IEEE Std 802.2™, PPPoE session, MPLS stacks, and ESP/AH IP-security headers
 - Supported in all FIFO modes
 - Quality of service support:
 - Transmission from up to eight physical queues
 - Reception to up to eight physical queues
 - Full- and half-duplex Ethernet support (1000 Mbps supports only full duplex):
 - IEEE 802.3 full-duplex flow control (automatic PAUSE frame generation or software-programmed PAUSE frame generation and recognition)
 - Programmable maximum frame length supports jumbo frames (up to 9.6 Kbytes) and IEEE Std. 802.1™ virtual local area network (VLAN) tags and priority
 - VLAN insertion and deletion
 - Per-frame VLAN control word or default VLAN for each eTSEC
 - Extracted VLAN control word passed to software separately
 - Retransmission following a collision
 - CRC generation and verification of inbound/outbound frames
 - Programmable Ethernet preamble insertion and extraction of up to 7 bytes
 - MAC address recognition:
 - Exact match on primary and virtual 48-bit unicast addresses

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the device. This device is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

The following table provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings ¹

Characteristic		Symbol	Max Value	Unit	Notes
Core supply voltage		V_{DD}	–0.3 to 1.21	V	—
PLL supply voltage		AV_{DD}	–0.3 to 1.21	V	—
Core power supply for SerDes transceivers		SV_{DD}	–0.3 to 1.21	V	—
Pad power supply for SerDes transceivers		XV_{DD}	–0.3 to 1.21	V	—
DDR and DDR2 DRAM I/O voltage		GV_{DD}	–0.3 to 2.75 –0.3 to 1.98	V	2
Three-speed Ethernet I/O voltage		LV_{DD} (for eTSEC1 and eTSEC2)	–0.3 to 3.63 –0.3 to 2.75	V	3
		TV_{DD} (for eTSEC3 and eTSEC4)	–0.3 to 3.63 –0.3 to 2.75		
PCI/PCI-X, DUART, system control and power management, I ² C, Ethernet MII management, and JTAG I/O voltage		OV_{DD}	–0.3 to 3.63	V	—
Local bus I/O voltage		BV_{DD}	–0.3 to 3.63 –0.3 to 2.75	V	—
Input voltage	DDR/DDR2 DRAM signals	MV_{IN}	–0.3 to ($GV_{DD} + 0.3$)	V	4
	DDR/DDR2 DRAM reference	MV_{REF}	–0.3 to ($GV_{DD}/2 + 0.3$)	V	—
	Three-speed Ethernet I/O signals	LV_{IN} TV_{IN}	–0.3 to ($LV_{DD} + 0.3$) –0.3 to ($TV_{DD} + 0.3$)	V	4
	Local bus signals	BV_{IN}	–0.3 to ($BV_{DD} + 0.3$)	—	—
	DUART, SYSCLK, system control and power management, I ² C, Ethernet MII management, and JTAG signals	OV_{IN}	–0.3 to ($OV_{DD} + 0.3$)	V	4
	PCI/PCI-X	OV_{IN}	–0.3 to ($OV_{DD} + 0.3$)	V	4

2.1.3 Output Driver Characteristics

The following table provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 3. Output Drive Capability

Driver Type	Programmable Output Impedance (Ω)	Supply Voltage	Notes
Local bus interface utilities signals	25 25	$BV_{DD} = 3.3\text{ V}$ $BV_{DD} = 2.5\text{ V}$	1
	45(default) 45(default)	$BV_{DD} = 3.3\text{ V}$ $BV_{DD} = 2.5\text{ V}$	
PCI signals	25	$OV_{DD} = 3.3\text{ V}$	2
	45(default)		
DDR signal	18 36 (half strength mode)	$GV_{DD} = 2.5\text{ V}$	3
DDR2 signal	18 36 (half strength mode)	$GV_{DD} = 1.8\text{ V}$	3
TSEC/10/100 signals	45	$L/TV_{DD} = 2.5/3.3\text{ V}$	—
DUART, system control, JTAG	45	$OV_{DD} = 3.3\text{ V}$	—
I2C	150	$OV_{DD} = 3.3\text{ V}$	—

Notes:

1. The drive strength of the local bus interface is determined by the configuration of the appropriate bits in PORIMPSR.
2. The drive strength of the PCI interface is determined by the setting of the PCI_GNT1 signal at reset.
3. The drive strength of the DDR interface in half-strength mode is at $T_j = 105^\circ\text{C}$ and at GV_{DD} (min).

2.2 Power Sequencing

The device requires its power rails to be applied in a specific sequence in order to ensure proper device operation. These requirements are as follows for power-up:

1. V_{DD} , AV_{DD-n} , BV_{DD} , LV_{DD} , OV_{DD} , SV_{DD} , TV_{DD} , XV_{DD}
2. GV_{DD}

All supplies must be at their stable values within 50 ms.

NOTE

Items on the same line have no ordering requirement with respect to one another. Items on separate lines must be ordered sequentially such that voltage rails on a previous step must reach 90% of their value before the voltage rails on the current step reach 10% of theirs.

NOTE

In order to guarantee MCKE low during power-up, the above sequencing for GV_{DD} is required. If there is no concern about any of the DDR signals being in an indeterminate state during power-up, then the sequencing for GV_{DD} is not required.

4.3 eTSEC Gigabit Reference Clock Timing

The following table provides the eTSEC gigabit reference clocks (EC_GTX_CLK125) AC timing specifications for the device.

Table 6. EC_GTX_CLK125 AC Timing Specifications

Parameter/Condition	Symbol	Min	Typ	Max	Unit	Notes
EC_GTX_CLK125 frequency	f_{G125}	—	125	—	MHz	—
EC_GTX_CLK125 cycle time	t_{G125}	—	8	—	ns	
EC_GTX_CLK125 rise and fall time L/TVDD = 2.5 V L/TVDD = 3.3 V	t_{G125R}, t_{G125F}	—	—	0.75 1.0	ns	1
EC_GTX_CLK125 duty cycle GMII, TBI 1000Base-T for RGMII, RTBI	t_{G125H}/t_{G125L}	45 47	—	55 53	%	2, 3

Notes:

1. Rise and fall times for EC_GTX_CLK125 are measured from 0.5 and 2.0 V for L/TVDD = 2.5 V, and from 0.6 and 2.7 V for L/TVDD = 3.3 V.
2. Timing is guaranteed by design and characterization.
3. EC_GTX_CLK125 is used to generate the GTX clock TSECn_GTX_CLK for the eTSEC transmitter with 2% degradation. EC_GTX_CLK125 duty cycle can be loosened from 47/53% as long as the PHY device can tolerate the duty cycle generated by the TSECn_GTX_CLK. See [Section 8.2.6, "RGMII and RTBI AC Timing Specifications,"](#) for duty cycle for 10Base-T and 100Base-T reference clock.

4.4 PCI/PCI-X Reference Clock Timing

When the PCI/PCI-X controller is configured for asynchronous operation, the reference clock for the PCI/PCI-x controller is not the SYSCLK input, but instead the PCIn_CLK. The following table provides the PCI/PCI-X reference clock AC timing specifications for the device.

Table 7. PCIn_CLK AC Timing Specifications

At recommended operating conditions (see [Table 2](#)) with OVDD = 3.3 V ± 165 mV.

Parameter/Condition	Symbol	Min	Typ	Max	Unit	Notes
PCIn_CLK frequency	f_{PCICLK}	16	—	133	MHz	—
PCIn_CLK cycle time	t_{PCICLK}	7.5	—	60	ns	—
PCIn_CLK rise and fall time	t_{PCIKH}, t_{PCIKL}	0.6	1.0	2.1	ns	1, 2
PCIn_CLK duty cycle	t_{PCIKHL}/t_{PCICLK}	40	—	60	%	2

Notes:

1. Rise and fall times for SYSCLK are measured at 0.6 and 2.7 V.
2. Timing is guaranteed by design and characterization.

5 RESET Initialization

This section describes the AC electrical specifications for the RESET initialization timing requirements of the device. The following table provides the RESET initialization AC timing specifications for the DDR SDRAM component(s).

Table 8. RESET Initialization Timing Specifications

Parameter/Condition	Min	Max	Unit	Notes
Required assertion time of $\overline{\text{HRESET}}$	100	—	μs	—
Minimum assertion time for $\overline{\text{SRESET}}$	3	—	SYSCLKs	1
PLL input setup time with stable SYSCLK before $\overline{\text{HRESET}}$ negation	100	—	μs	—
Input setup time for POR configs (other than PLL config) with respect to negation of $\overline{\text{HRESET}}$	4	—	SYSCLKs	1
Input hold time for all POR configs (including PLL config) with respect to negation of $\overline{\text{HRESET}}$	2	—	SYSCLKs	1
Maximum valid-to-high impedance time for actively driven POR configs with respect to negation of $\overline{\text{HRESET}}$	—	5	SYSCLKs	1

Note:

1. SYSCLK is the primary clock input for the device.

The following table provides the PLL lock times.

Table 9. PLL Lock Times

Parameter/Condition	Min	Max	Unit
Core and platform PLL lock times	—	100	μs
Local bus PLL lock time	—	50	μs
PCI/PCI-X bus PLL lock time	—	50	μs

5.1 Power-On Ramp Rate

This section describes the AC electrical specifications for the power-on ramp rate requirements. Controlling the maximum power-on ramp rate is required to avoid falsely triggering the ESD circuitry. The following table provides the power supply ramp rate specifications.

Table 10. Power Supply Ramp Rate

Parameter	Min	Max	Unit	Notes
Required ramp rate for MVREF	—	3500	V/s	1
Required ramp rate for VDD	—	4000	V/s	1, 2

Note:

1. Maximum ramp rate from 200 to 500 mV is most critical as this range may falsely trigger the ESD circuitry.
2. VDD itself is not vulnerable to false ESD triggering; however, as per [Section 22.2, “PLL Power Supply Filtering,”](#) the recommended AVDD_CORE, AVDD_PLAT, AVDD_LBIU, AVDD_PCI1 and AVDD_PCI2 filters are all connected to VDD. Their ramp rates must be equal to or less than the VDD ramp rate.

6 DDR and DDR2 SDRAM

This section describes the DC and AC electrical specifications for the DDR SDRAM interface of the device. Note that $GV_{DD}(\text{typ}) = 2.5 \text{ V}$ for DDR SDRAM, and $GV_{DD}(\text{typ}) = 1.8 \text{ V}$ for DDR2 SDRAM.

6.1 DDR SDRAM DC Electrical Characteristics

The following table provides the recommended operating conditions for the DDR2 SDRAM controller of the device when $GV_{DD}(\text{typ}) = 1.8 \text{ V}$.

Table 11. DDR2 SDRAM DC Electrical Characteristics for $GV_{DD}(\text{typ}) = 1.8 \text{ V}$

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	1.71	1.89	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.125$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	-0.3	$MV_{REF} - 0.125$	V	—
Output leakage current	I_{OZ}	-50	50	μA	4
Output high current ($V_{OUT} = 1.420 \text{ V}$)	I_{OH}	-13.4	—	mA	—
Output low current ($V_{OUT} = 0.280 \text{ V}$)	I_{OL}	13.4	—	mA	—

Notes:

- GV_{DD} is expected to be within 50 mV of the DRAM V_{DD} at all times.
- MV_{REF} is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed $\pm 2\%$ of the DC value.
- V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF} . This rail must track variations in the DC level of MV_{REF} .
- Output leakage is measured with all outputs disabled, $0 \text{ V} \leq V_{OUT} \leq GV_{DD}$.

This table provides the DDR2 I/O capacitance when $GV_{DD}(\text{typ}) = 1.8 \text{ V}$.

Table 12. DDR2 SDRAM Capacitance for $GV_{DD}(\text{typ})=1.8 \text{ V}$

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, \overline{DQS}	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, \overline{DQS}	C_{DIO}	—	0.5	pF	1

Note:

- This parameter is sampled. $GV_{DD} = 1.8 \text{ V} \pm 0.090 \text{ V}$, $f = 1 \text{ MHz}$, $T_A = 25^\circ\text{C}$, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

Table 23. GMII, MII, RMII, TBI, RGMII, RTBI, and FIFO DC Electrical Characteristics

Parameters	Symbol	Min	Max	Unit	Notes
Supply voltage 2.5 V	LV_{DD}/TV_{DD}	2.37	2.63	V	1, 2
Output high voltage ($LV_{DD}/TV_{DD} = \text{Min}$, $I_{OH} = -1.0 \text{ mA}$)	V_{OH}	2.00	$LV_{DD}/TV_{DD} + 0.3$	V	—
Output low voltage ($LV_{DD}/TV_{DD} = \text{Min}$, $I_{OL} = 1.0 \text{ mA}$)	V_{OL}	GND -0.3	0.40	V	—
Input high voltage	V_{IH}	1.70	$LV_{DD}/TV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	-0.3	0.90	V	—
Input high current ($V_{IN} = LV_{DD}$, $V_{IN} = TV_{DD}$)	I_{IH}	—	10	μA	1, 2, 3
Input low current ($V_{IN} = \text{GND}$)	I_{IL}	-15	—	μA	3

Notes:

1. LV_{DD} supports eTSECs 1 and 2.
2. TV_{DD} supports eTSECs 3 and 4.
3. Note that the symbol V_{IN} , in this case, represents the LV_{IN} and TV_{IN} symbols referenced in [Table 1](#) and [Table 2](#).

8.2 FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI AC Timing Specifications

The AC timing specifications for FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI are presented in this section.

8.2.1 FIFO AC Specifications

The basis for the AC specifications for the eTSEC's FIFO modes is the double data rate RGMII and RTBI specifications, since they have similar performances and are described in a source-synchronous fashion like FIFO modes. However, the FIFO interface provides deliberate skew between the transmitted data and source clock in GMII fashion.

When the eTSEC is configured for FIFO modes, all clocks are supplied from external sources to the relevant eTSEC interface. That is, the transmit clock must be applied to the eTSECn's TSECn_TX_CLK, while the receive clock must be applied to pin TSECn_RX_CLK. The eTSEC internally uses the transmit clock to synchronously generate transmit data and outputs an echoed copy of the transmit clock back out onto the TSECn_GTX_CLK pin (while transmit data appears on TSECn_TXD[7:0], for example). It is intended that external receivers capture eTSEC transmit data using the clock on TSECn_GTX_CLK as a source-synchronous timing reference. Typically, the clock edge that launched the data can be used, since the clock is delayed by the eTSEC to allow acceptable set-up margin at the receiver. Note that there is relationship between the maximum FIFO speed and the platform speed. For more information see [Section 4.5, "Platform to FIFO Restrictions."](#)

9 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals MDIO (management data input/output) and MDC (management data clock). The electrical characteristics for GMII, RGMII, RMII, TBI, and RTBI are specified in “[Section 8, “Enhanced Three-Speed Ethernet \(eTSEC\).”](#)”

9.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in this table.

Table 36. MII Management DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
Supply voltage (3.3 V)	OV_{DD}	3.13	3.47	V
Output high voltage ($OV_{DD} = \text{Min}$, $I_{OH} = -1.0 \text{ mA}$)	V_{OH}	2.10	$OV_{DD} + 0.3$	V
Output low voltage ($OV_{DD} = \text{Min}$, $I_{OL} = 1.0 \text{ mA}$)	V_{OL}	GND	0.50	V
Input high voltage	V_{IH}	2.0	—	V
Input low voltage	V_{IL}	—	0.90	V
Input high current ($OV_{DD} = \text{Max}$, $V_{IN}^1 = 2.1 \text{ V}$)	I_{IH}	—	40	μA
Input low current ($OV_{DD} = \text{Max}$, $V_{IN} = 0.5 \text{ V}$)	I_{IL}	-600	—	μA

Note:

1. Note that the symbol V_{IN} , in this case, represents the OV_{IN} symbol referenced in [Table 1](#) and [Table 2](#).

9.2 MII Management AC Electrical Specifications

This table provides the MII management AC timing specifications.

Table 37. MII Management AC Timing Specifications

At recommended operating conditions with OV_{DD} is 3.3 V \pm 5%.

Parameter	Symbol ¹	Min	Typ	Max	Unit	Notes
MDC frequency	f_{MDC}	0.72	2.5	8.3	MHz	2, 3, 4
MDC period	t_{MDC}	120.5	—	1389	ns	—
MDC clock pulse width high	t_{MDCH}	32	—	—	ns	—
MDC to MDIO valid	t_{MDKHDV}	$16 \times t_{CCB}$	—	—	ns	5
MDC to MDIO delay	t_{MDKHDX}	$(16 \times t_{CCB} \times 8) - 3$	—	$(16 \times t_{CCB} \times 8) + 3$	ns	5
MDIO to MDC setup time	t_{MDDVKH}	5	—	—	ns	—
MDIO to MDC hold time	t_{MDDXKH}	0	—	—	ns	—
MDC rise time	t_{MDCR}	—	—	10	ns	4

Table 37. MII Management AC Timing Specifications (continued)At recommended operating conditions with OV_{DD} is 3.3 V \pm 5%.

Parameter	Symbol ¹	Min	Typ	Max	Unit	Notes
MDC fall time	t_{MDHF}	—		10	ns	4

Notes:

- The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, t_{MDDVKH} symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
- This parameter is dependent on the eTSEC system clock speed, which is half of the Platform Frequency (f_{CCB}). The actual ECn_MDC output clock frequency for a specific eTSEC port can be programmed by configuring the MgmtClk bit field of device's MIIMCFG register, based on the platform (CCB) clock running for the device. The formula is: Platform Frequency (CCB) \div (2 \times Frequency Divider determined by MIIMCFG[MgmtClk] encoding selection). For example, if MIIMCFG[MgmtClk] = 000 and the platform (CCB) is currently running at 533 MHz, $f_{MDC} = 533 \div (2 \times 4 \times 8) = 533 \div 64 = 8.3$ MHz. That is, for a system running at a particular platform frequency (f_{CCB}), the ECn_MDC output clock frequency can be programmed between maximum $f_{MDC} = f_{CCB} \div 64$ and minimum $f_{MDC} = f_{CCB} \div 448$. See 14.5.3.6.6, "MII Management Configuration Register (MIIMCFG)," in the *MPC8548E PowerQUICC™ III Integrated Processor Family Reference Manual* for more detail.
- The maximum ECn_MDC output clock frequency is defined based on the maximum platform frequency for device (533 MHz) divided by 64, while the minimum ECn_MDC output clock frequency is defined based on the minimum platform frequency for device (333 MHz) divided by 448, following the formula described in Note 2 above.
- Guaranteed by design.
- t_{CCB} is the platform (CCB) clock period.

Figure 21 shows the MII management AC timing diagram.

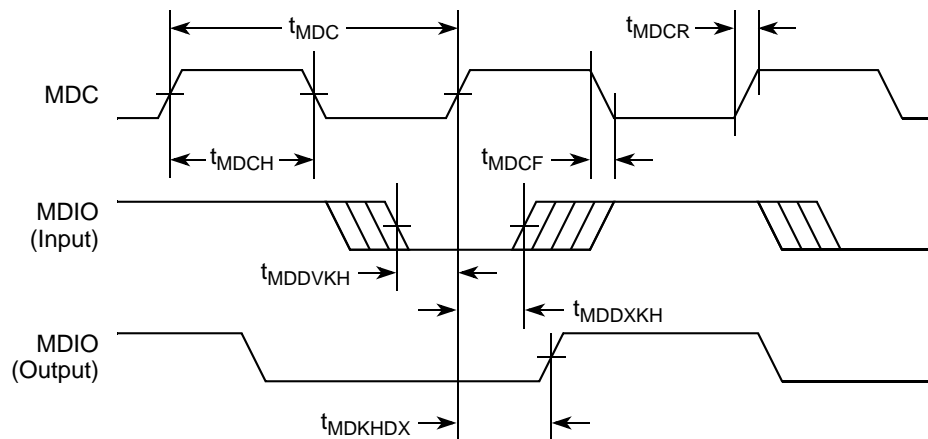
**Figure 21. MII Management Interface Timing Diagram**

Table 44. JTAG AC Timing Specifications (Independent of SYSCLK)¹ (continued)

Parameter	Symbol ²	Min	Max	Unit	Notes
Valid times: Boundary-scan data TDO	t_{JTKLDV} t_{JTKLOV}	4 2	20 10	ns	5
Output hold times: Boundary-scan data TDO	t_{JTKLDX} t_{JTKLOX}	30 30	— —	ns	5
JTAG external clock to output high impedance: Boundary-scan data TDO	t_{JTKLDZ} t_{JTKLOZ}	3 3	19 9	ns	5, 6

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50-Ω load (see Figure 29). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols used for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{JTDVXH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDVXH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. \overline{TRST} is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK} .
5. Non-JTAG signal output timing with respect to t_{TCLK} .
6. Guaranteed by design.

Figure 29 provides the AC test load for TDO and the boundary-scan outputs.

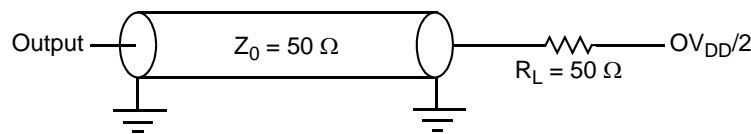


Figure 29. AC Test Load for the JTAG Interface

Figure 30 provides the JTAG clock input timing diagram.

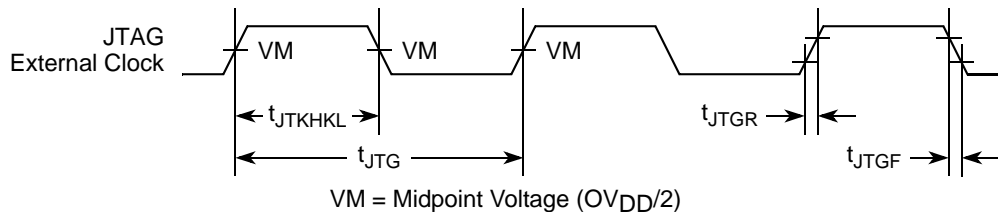


Figure 30. JTAG Clock Input Timing Diagram

Figure 31 provides the $\overline{\text{TRST}}$ timing diagram.

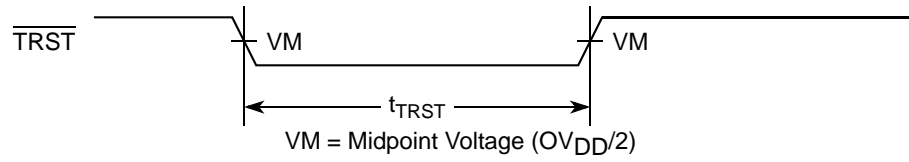


Figure 31. $\overline{\text{TRST}}$ Timing Diagram

Figure 32 provides the boundary-scan timing diagram.

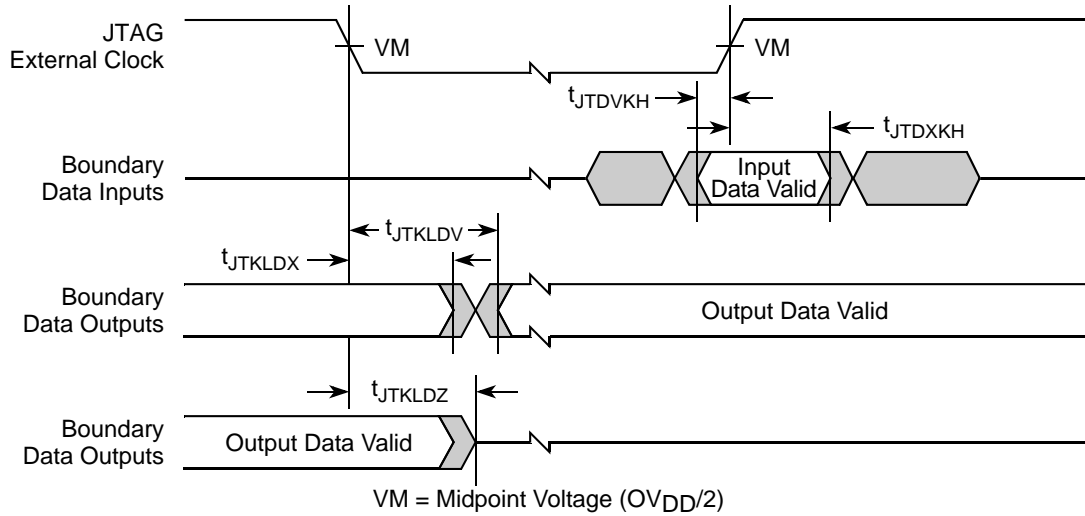


Figure 32. Boundary-Scan Timing Diagram

14 GP_{OUT}/GP_{IN}

This section describes the DC and AC electrical specifications for the GP_{OUT}/GP_{IN} bus of the device.

14.1 GP_{OUT}/GP_{IN} Electrical Characteristics

Table 47 and Table 48 provide the DC electrical characteristics for the GP_{OUT} interface.

Table 47. GP_{OUT} DC Electrical Characteristics (3.3 V DC)

Parameter	Symbol	Min	Max	Unit
Supply voltage 3.3 V	BV _{DD}	3.13	3.47	V
High-level output voltage (BV _{DD} = min, I _{OH} = –2 mA)	V _{OH}	BV _{DD} – 0.2	—	V
Low-level output voltage (BV _{DD} = min, I _{OL} = 2 mA)	V _{OL}	—	0.2	V

Table 48. GP_{OUT} DC Electrical Characteristics (2.5 V DC)

Parameter	Symbol	Min	Max	Unit
Supply voltage 2.5 V	BV _{DD}	2.37	2.63	V
High-level output voltage (BV _{DD} = min, I _{OH} = –1 mA)	V _{OH}	2.0	BV _{DD} + 0.3	V
Low-level output voltage (BV _{DD} min, I _{OL} = 1 mA)	V _{OL}	GND – 0.3	0.4	V

Table 49 and Table 50 provide the DC electrical characteristics for the GP_{IN} interface.

Table 49. GP_{IN} DC Electrical Characteristics (3.3 V DC)

Parameter	Symbol	Min	Max	Unit
Supply voltage 3.3 V	BV _{DD}	3.13	3.47	V
High-level input voltage	V _{IH}	2	BV _{DD} + 0.3	V
Low-level input voltage	V _{IL}	–0.3	0.8	V
Input current (BV _{IN} ¹ = 0 V or BV _{IN} = BV _{DD})	I _{IN}	—	±5	μA

Note:

1. The symbol BV_{IN}, in this case, represents the BV_{IN} symbol referenced in Table 1.

- The SD_REF_CLK and $\overline{\text{SD_REF_CLK}}$ are internally AC-coupled differential inputs as shown in Figure 39. Each differential clock input (SD_REF_CLK or $\overline{\text{SD_REF_CLK}}$) has a 50- Ω termination to SGND_SRDSn (xcorevss) followed by on-chip AC-coupling.
- The external reference clock driver must be able to drive this termination.
- The SerDes reference clock input can be either differential or single-ended. See the differential mode and single-ended mode description below for further detailed requirements.
- The maximum average current requirement that also determines the common mode voltage range:
 - When the SerDes reference clock differential inputs are DC coupled externally with the clock driver chip, the maximum average current allowed for each input pin is 8 mA. In this case, the exact common mode input voltage is not critical as long as it is within the range allowed by the maximum average current of 8 mA (see the following bullet for more detail), since the input is AC-coupled on-chip.
 - This current limitation sets the maximum common mode input voltage to be less than 0.4 V ($0.4 \text{ V}/50 = 8 \text{ mA}$) while the minimum common mode input level is 0.1 V above SGND_SRDSn (xcorevss). For example, a clock with a 50/50 duty cycle can be produced by a clock driver with output driven by its current source from 0 to 16 mA (0–0.8 V), such that each phase of the differential input has a single-ended swing from 0 V to 800 mV with the common mode voltage at 400 mV.
 - If the device driving the SD_REF_CLK and $\overline{\text{SD_REF_CLK}}$ inputs cannot drive 50 Ω to SGND_SRDSn (xcorevss) DC, or it exceeds the maximum input current limitations, then it must be AC-coupled off-chip.
- The input amplitude requirement:
 - This requirement is described in detail in the following sections.

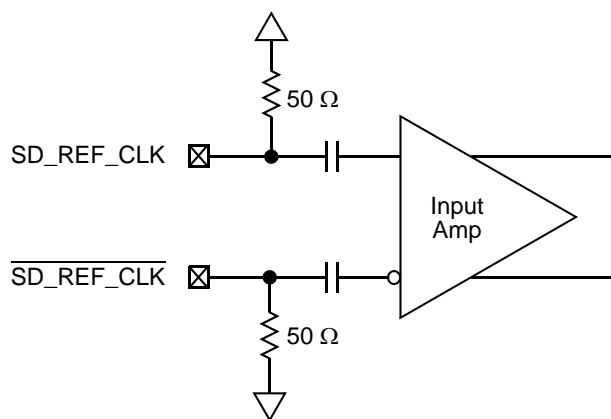


Figure 39. Receiver of SerDes Reference Clocks

16.2.2 DC Level Requirement for SerDes Reference Clocks

The DC level requirement for the SerDes reference clock inputs is different depending on the signaling mode used to connect the clock driver chip and SerDes reference clock inputs as described below:

- Differential mode

components are included in this requirement. The reference impedance for return loss measurements is 100- Ω resistive for differential return loss and 25- Ω resistive for common mode.

Table 66. Receiver AC Timing Specifications—1.25 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Differential input voltage	V_{IN}	200	1600	mVp-p	Measured at receiver
Deterministic jitter tolerance	J_D	0.37	—	UI p-p	Measured at receiver
Combined deterministic and random jitter tolerance	J_{DR}	0.55	—	UI p-p	Measured at receiver
Total jitter tolerance ¹	J_T	0.65	—	UI p-p	Measured at receiver
Multiple input skew	S_{MI}	—	24	ns	Skew at the receiver input between lanes of a multilane link
Bit error rate	BER	—	10^{-12}	—	—
Unit interval	UI	800	800	ps	± 100 ppm

Note:

1. Total jitter is composed of three components, deterministic jitter, random jitter, and single frequency sinusoidal jitter. The sinusoidal jitter may have any amplitude and frequency in the unshaded region of [Figure 53](#). The sinusoidal jitter component is included to ensure margin for low frequency jitter, wander, noise, crosstalk, and other variable system effects.

Table 67. Receiver AC Timing Specifications—2.5 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Differential input voltage	V_{IN}	200	1600	mVp-p	Measured at receiver
Deterministic jitter tolerance	J_D	0.37	—	UI p-p	Measured at receiver
Combined deterministic and random jitter tolerance	J_{DR}	0.55	—	UI p-p	Measured at receiver
Total jitter tolerance ¹	J_T	0.65	—	UI p-p	Measured at receiver
Multiple input skew	S_{MI}	—	24	ns	Skew at the receiver input between lanes of a multilane link
Bit error rate	BER	—	10^{-12}	—	—
Unit interval	UI	400	400	ps	± 100 ppm

Note:

1. Total jitter is composed of three components, deterministic jitter, random jitter, and single frequency sinusoidal jitter. The sinusoidal jitter may have any amplitude and frequency in the unshaded region of [Figure 53](#). The sinusoidal jitter component is included to ensure margin for low frequency jitter, wander, noise, crosstalk, and other variable system effects.

18.8 Receiver Eye Diagrams

For each baud rate at which an LP-serial receiver is specified to operate, the receiver shall meet the corresponding bit error rate specification (Table 66, Table 67, and Table 68) when the eye pattern of the receiver test signal (exclusive of sinusoidal jitter) falls entirely within the unshaded portion of the receiver input compliance mask shown in Figure 54 with the parameters specified in Table 69. The eye pattern of the receiver test signal is measured at the input pins of the receiving device with the device replaced with a $100\text{-}\Omega \pm 5\%$ differential resistive load.

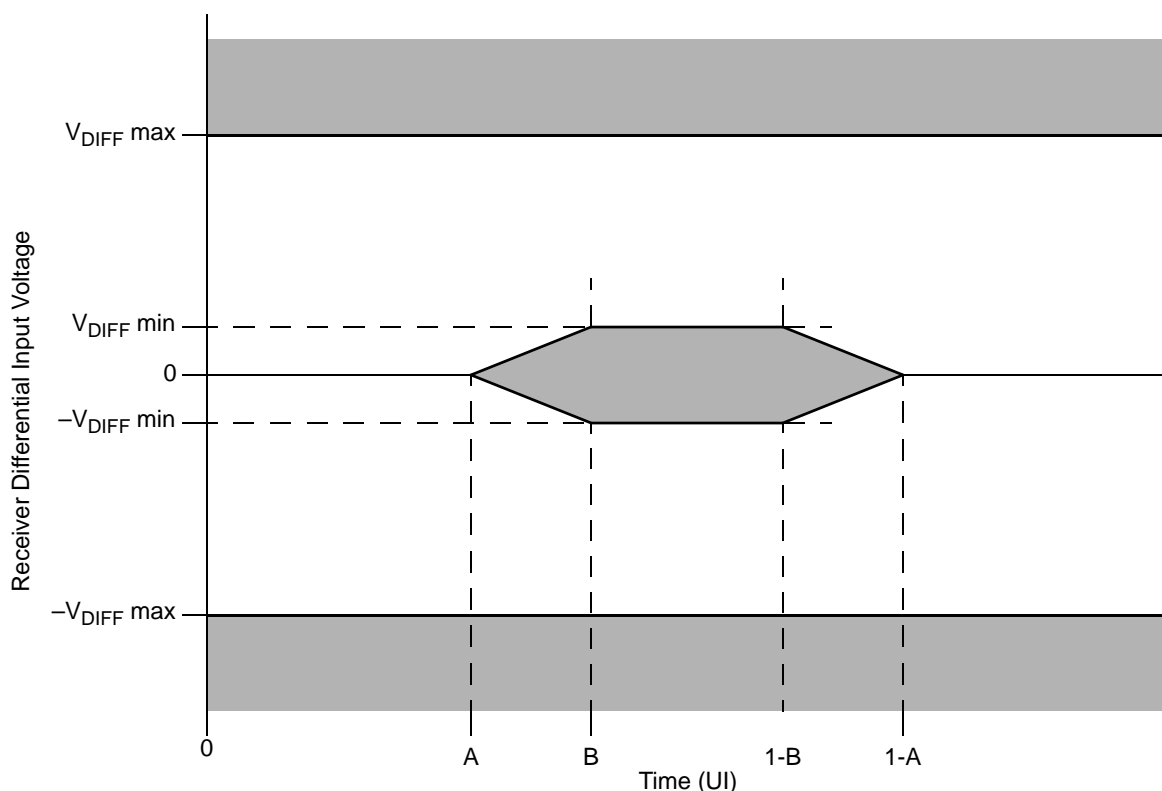


Figure 54. Receiver Input Compliance Mask

Table 69. Receiver Input Compliance Mask Parameters Exclusive of Sinusoidal Jitter

Receiver Type	$V_{DIFFmin}$ (mV)	$V_{DIFFmax}$ (mV)	A (UI)	B (UI)
1.25 GBaud	100	800	0.275	0.400
2.5 GBaud	100	800	0.275	0.400
3.125 GBaud	100	800	0.275	0.400

18.9 Measurement and Test Requirements

Since the LP-serial electrical specification are guided by the XAUI electrical interface specified in Clause 47 of IEEE Std. 802.3ae-2002, the measurement and test requirements defined here are similarly guided by Clause 47. Additionally, the CJPAT test pattern defined in Annex 48A of IEEE Std.

Table 72. MPC8547E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Reserved	U20, V22, W20, Y22	—	—	15
Reserved	U21, V23, W21, Y23	—	—	15
SD_PLL_TPD	U28	O	XV _{DD}	24
SD_REF_CLK	T28	I	XV _{DD}	—
$\overline{\text{SD_REF_CLK}}$	T27	I	XV _{DD}	—
Reserved	AC1, AC3	—	—	2
Reserved	M26, V28	—	—	32
Reserved	M25, V27	—	—	34
Reserved	M20, M21, T22, T23	—	—	38
General-Purpose Output				
GPOUT[24:31]	K26, K25, H27, G28, H25, J26, K24, K23	O	BV _{DD}	—
System Control				
$\overline{\text{HRESET}}$	AG17	I	OV _{DD}	—
$\overline{\text{HRESET_REQ}}$	AG16	O	OV _{DD}	29
$\overline{\text{SRESET}}$	AG20	I	OV _{DD}	—
$\overline{\text{CKSTP_IN}}$	AA9	I	OV _{DD}	—
$\overline{\text{CKSTP_OUT}}$	AA8	O	OV _{DD}	2, 4
Debug				
TRIG_IN	AB2	I	OV _{DD}	—
TRIG_OUT/READY/QUIESCE	AB1	O	OV _{DD}	6, 9, 19, 29
MSRCID[0:1]	AE4, AG2	O	OV _{DD}	5, 6, 9
MSRCID[2:4]	AF3, AF1, AF2	O	OV _{DD}	6, 19, 29
MDVAL	AE5	O	OV _{DD}	6
CLK_OUT	AE21	O	OV _{DD}	11
Clock				
RTC	AF16	I	OV _{DD}	—
SYSCLK	AH17	I	OV _{DD}	—
JTAG				
TCK	AG28	I	OV _{DD}	—
TDI	AH28	I	OV _{DD}	12
TDO	AF28	O	OV _{DD}	—
TMS	AH27	I	OV _{DD}	12
$\overline{\text{TRST}}$	AH23	I	OV _{DD}	12

Table 73. MPC8545E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
SD_TX[0:3]	M23, N21, P23, R21	O	XV _{DD}	—
Reserved	W26, Y28, AA26, AB28	—	—	40
Reserved	W25, Y27, AA25, AB27	—	—	40
Reserved	U20, V22, W20, Y22	—	—	15
Reserved	U21, V23, W21, Y23	—	—	15
SD_PLL_TPD	U28	O	XV _{DD}	24
SD_REF_CLK	T28	I	XV _{DD}	—
SD_REF_CLK	T27	I	XV _{DD}	—
Reserved	AC1, AC3	—	—	2
Reserved	M26, V28	—	—	32
Reserved	M25, V27	—	—	34
Reserved	M20, M21, T22, T23	—	—	38
General-Purpose Output				
GPOUT[24:31]	K26, K25, H27, G28, H25, J26, K24, K23	O	BV _{DD}	—
System Control				
HRESET	AG17	I	OV _{DD}	—
HRESET_REQ	AG16	O	OV _{DD}	29
SRESET	AG20	I	OV _{DD}	—
CKSTP_IN	AA9	I	OV _{DD}	—
CKSTP_OUT	AA8	O	OV _{DD}	2, 4
Debug				
TRIG_IN	AB2	I	OV _{DD}	—
TRIG_OUT/READY/QUIESCE	AB1	O	OV _{DD}	6, 9, 19, 29
MSRCID[0:1]	AE4, AG2	O	OV _{DD}	5, 6, 9
MSRCID[2:4]	AF3, AF1, AF2	O	OV _{DD}	6, 19, 29
MDVAL	AE5	O	OV _{DD}	6
CLK_OUT	AE21	O	OV _{DD}	11
Clock				
RTC	AF16	I	OV _{DD}	—
SYSCLK	AH17	I	OV _{DD}	—
JTAG				
TCK	AG28	I	OV _{DD}	—
TDI	AH28	I	OV _{DD}	12

Table 74. MPC8543E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
JTAG				
TCK	AG28	I	OV _{DD}	—
TDI	AH28	I	OV _{DD}	12
TDO	AF28	O	OV _{DD}	—
TMS	AH27	I	OV _{DD}	12
TRST	AH23	I	OV _{DD}	12
DFT				
L1_TSTCLK	AC25	I	OV _{DD}	25
L2_TSTCLK	AE22	I	OV _{DD}	25
LSSD_MODE	AH20	I	OV _{DD}	25
TEST_SEL	AH14	I	OV _{DD}	109
Thermal Management				
THERM0	AG1	—	—	14
THERM1	AH1	—	—	14
Power Management				
ASLEEP	AH18	O	OV _{DD}	9, 19, 29
Power and Ground Signals				
GND	A11, B7, B24, C1, C3, C5, C12, C15, C26, D8, D11, D16, D20, D22, E1, E5, E9, E12, E15, E17, F4, F26, G12, G15, G18, G21, G24, H2, H6, H8, H28, J4, J12, J15, J17, J27, K7, K9, K11, K27, L3, L5, L12, L16, N11, N13, N15, N17, N19, P4, P9, P12, P14, P16, P18, R11, R13, R15, R17, R19, T4, T12, T14, T16, T18, U8, U11, U13, U15, U17, U19, V4, V12, V18, W6, W19, Y4, Y9, Y11, Y19, AA6, AA14, AA17, AA22, AA23, AB4, AC2, AC11, AC19, AC26, AD5, AD9, AD22, AE3, AE14, AF6, AF10, AF13, AG8, AG27, K28, L24, L26, N24, N27, P25, R28, T24, T26, U24, V25, W28, Y24, Y26, AA24, AA27, AB25, AC28, L21, L23, N22, P20, R23, T21, U22, V20, W23, Y21, U27	—	—	—
OV _{DD}	V16, W11, W14, Y18, AA13, AA21, AB11, AB17, AB24, AC4, AC9, AC21, AD6, AD13, AD17, AD19, AE10, AE8, AE24, AF4, AF12, AF22, AF27, AG26	Power for PCI and other standards (3.3 V)	OV _{DD}	—
LV _{DD}	N8, R7, T9, U6	Power for TSEC1 and TSEC2 (2.5 V, 3.3 V)	LV _{DD}	—

Table 85. Package Thermal Characteristics for FC-PBGA (continued)

Characteristic	JEDEC Board	Symbol	Value	Unit	Notes
Die junction-to-board	N/A	$R_{\theta JB}$	5	°C/W	3
Die junction-to-case	N/A	$R_{\theta JC}$	0.8	°C/W	4

Notes:

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, airflow, power dissipation of other components on the board, and board thermal resistance.
2. Per JEDEC JESD51-6 with the board (JESD51-7) horizontal.
3. Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
4. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1). The cold plate temperature is used for the case temperature, measured value includes the thermal resistance of the interface layer.

21.3 Heat Sink Solution

Every system application has different conditions that the thermal management solution must solve. As such, providing a recommended heat sink has not been found to be very useful. When a heat sink is chosen, give special consideration to the mounting technique. Mounting the heat sink to the printed-circuit board is the recommended procedure using a maximum of 10 lbs force (45 Newtons) perpendicular to the package and board. Clipping the heat sink to the package is not recommended.

22 System Design Information

This section provides electrical design recommendations for successful application of the device.

22.1 System Clocking

This device includes five PLLs, as follows:

1. The platform PLL generates the platform clock from the externally supplied SYSCLK input. The frequency ratio between the platform and SYSCLK is selected using the platform PLL ratio configuration bits as described in [Section 20.2, “CCB/SYSCLK PLL Ratio.”](#)
2. The e500 core PLL generates the core clock as a slave to the platform clock. The frequency ratio between the e500 core clock and the platform clock is selected using the e500 PLL ratio configuration bits as described in [Section 20.3, “e500 Core PLL Ratio.”](#)
3. The PCI PLL generates the clocking for the PCI bus.
4. The local bus PLL generates the clock for the local bus.
5. There is a PLL for the SerDes block.

22.2 PLL Power Supply Filtering

Each of the PLLs listed above is provided with power through independent power supply pins (AV_{DD_PLAT} , AV_{DD_CORE} , AV_{DD_PCI} , AV_{DD_LBIU} , and AV_{DD_SRDS} , respectively). The AV_{DD}

23 Ordering Information

Ordering information for the parts fully covered by this specification document is provided in [Section 23.1, “Part Numbers Fully Addressed by this Document.”](#)

23.1 Part Numbers Fully Addressed by this Document

This table provides the Freescale part numbering nomenclature for the device. Note that the individual part numbers correspond to a maximum processor core frequency. For available frequencies, contact your local Freescale sales office. In addition to the processor frequency, the part-numbering scheme also includes an application modifier that may specify special application conditions. Each part number also contains a revision code that refers to the die mask revision number.

Table 87. Part Numbering Nomenclature

MPC	nnnnn	t	pp	ff	c	r
Product Code	Part Identifier	Temperature	Package ^{1, 2, 3}	Processor Frequency ⁴	Core Frequency	Silicon Version
MPC	8548E	Blank = 0 to 105°C C = -40° to 105°C	HX = CBGA VU = Pb-free CBGA PX = PBGA VT = Pb-free PBGA	AV = 1500 ³ AU = 1333 AT = 1200 AQ = 1000	J = 533 H = 500 ⁵ G = 400	Blank = Ver. 2.0 (SVR = 0x80390020) A = Ver. 2.1.1 B = Ver. 2.1.2 C = Ver. 2.1.3 (SVR = 0x80390021) D = Ver. 3.1.x (SVR = 0x80390031)
	8548					Blank = Ver. 2.0 (SVR = 0x80310020) A = Ver. 2.1.1 B = Ver. 2.1.2 C = Ver. 2.1.3 (SVR = 0x80310021) D = Ver. 3.1.x (SVR = 0x80310031)
	8547E			AU = 1333 AT = 1200 AQ = 1000	J = 533 G = 400	Blank = Ver. 2.0 (SVR = 0x80390120) A = Ver. 2.1.1 B = Ver. 2.1.2 C = Ver. 2.1.3 (SVR = 0x80390121) D = Ver. 3.1.x (SVR = 0x80390131)
	8547					Blank = Ver. 2.0 (SVR = 0x80390120) A = Ver. 2.1.1 B = Ver. 2.1.2 C = Ver. 2.1.3 (SVR = 0x80310121) D = Ver. 3.1.x (SVR = 0x80310131)